

International  
**IR** Rectifier  
**RADIATION HARDENED**  
**POWER MOSFET**  
**SURFACE MOUNT (SMD-2)**

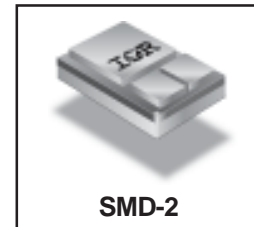
PD - 91787H

**IRHNA57Z60**  
**JANSR2N7467U2**  
**30V, N-CHANNEL**  
**REF: MIL-PRF-19500/683**



**Product Summary**

Part Number	Radiation Level	RDS(on)	Id	QPL Part Number
IRHNA57Z60	100K Rads (Si)	0.0035Ω	75A*	JANSR2N7467U2
IRHNA53Z60	300K Rads (Si)	0.0035Ω	75A*	JANSF2N7467U2
IRHNA54Z60	500K Rads (Si)	0.0035Ω	75A*	JANSG2N7467U2
IRHNA58Z60	1000K Rads (Si)	0.0040Ω	75A*	JANSH2N7467U2



International Rectifier's R5™ technology provides high performance power MOSFETs for space applications. These devices have been characterized for Single Event Effects (SEE) with useful performance up to an LET of 80 (MeV/(mg/cm<sup>2</sup>)). The combination of low RDS(on) and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well established advantages of MOSFETs such as voltage control, fast switching, ease of paralleling and temperature stability of electrical parameters.

**Features:**

- Single Event Effect (SEE) Hardened
- Ultra Low RDS(on)
- Low Total Gate Charge
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Surface Mount
- Ceramic Package
- Light Weight

**Absolute Maximum Ratings**

**Pre-Irradiation**

	Parameter		Units
Id @ VGS = 12V, TC = 25°C	Continuous Drain Current	75*	A
Id @ VGS = 12V, TC = 100°C	Continuous Drain Current	75*	
IdM	Pulsed Drain Current ①	300	
PD @ TC = 25°C	Max. Power Dissipation	250	W
	Linear Derating Factor	2.0	W/°C
VGS	Gate-to-Source Voltage	±20	V
EAS	Single Pulse Avalanche Energy ②	500	mJ
IAR	Avalanche Current ①	75	A
EAR	Repetitive Avalanche Energy ①	25	mJ
dv/dt	Peak Diode Recovery dv/dt ③	0.83	V/ns
TJ	Operating Junction	-55 to 150	°C
TSTG	Storage Temperature Range		
	Pckg. Mounting Surface Temp.	300 (for 5s)	
	Weight	3.3 (Typical)	g

\* Current is limited by package

For footnotes refer to the last page

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**Electrical Characteristics @ T<sub>j</sub> = 25°C (Unless Otherwise Specified)**

	Parameter	Min	Typ	Max	Units	Test Conditions
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1.0mA
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Temperature Coefficient of Breakdown Voltage	—	0.026	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1.0mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-State Resistance	—	—	0.0035	Ω	V <sub>GS</sub> = 12V, I <sub>D</sub> = 75A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	—	4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1.0mA
g <sub>fs</sub>	Forward Transconductance	45	—	—	S (r̄)	V <sub>DS</sub> ≥ 15V, I <sub>DS</sub> = 45A ④
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	—	—	10	μA	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V
		—	—	25		V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Leakage Forward	—	—	100	nA	V <sub>GS</sub> = 20V
I <sub>GSS</sub>	Gate-to-Source Leakage Reverse	—	—	-100		V <sub>GS</sub> = -20V
Q <sub>g</sub>	Total Gate Charge	—	—	200	nC	V <sub>GS</sub> = 12V, I <sub>D</sub> = 45A V <sub>DS</sub> = 15V
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	55		
Q <sub>gd</sub>	Gate-to-Drain ('Miller') Charge	—	—	40		
t <sub>d(on)</sub>	Turn-On Delay Time	—	—	35	ns	V <sub>DD</sub> = 15V, I <sub>D</sub> = 45A, V <sub>GS</sub> = 12V, R <sub>G</sub> = 2.35Ω
t <sub>r</sub>	Rise Time	—	—	125		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	—	80		
t <sub>f</sub>	Fall Time	—	—	50		
L <sub>S</sub> + L <sub>D</sub>	Total Inductance	—	4.0	—	nH	Measured from the center of drain pad to center of source pad
C <sub>iss</sub>	Input Capacitance	—	9110	—	pF	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 25V f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	4620	—		
C <sub>rss</sub>	Reverse Transfer Capacitance	—	150	—		

**Source-Drain Diode Ratings and Characteristics**

	Parameter	Min	Typ	Max	Units	Test Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	75*	A	
I <sub>SM</sub>	Pulse Source Current (Body Diode) ①	—	—	300		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>j</sub> = 25°C, I <sub>S</sub> = 75A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	—	165	ns	T <sub>j</sub> = 25°C, I <sub>F</sub> = 45A, di/dt ≤ 100A/μs
Q <sub>RR</sub>	Reverse Recovery Charge	—	—	690	nC	V <sub>DD</sub> ≤ 25V ④
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L <sub>S</sub> + L <sub>D</sub> .				

\* Current is limited by package

**Thermal Resistance**

	Parameter	Min	Typ	Max	Units	Test Conditions
R <sub>thJC</sub>	Junction-to-Case	—	—	0.5	°C/W	soldered to a 2" square copper-clad board
R <sub>thJ-PCB</sub>	Junction-to-PC board	—	1.6	—		

**Note:** Corresponding Spice and Saber models are available on International Rectifier Web site.

For footnotes refer to the last page

## Radiation Characteristics

## IRHNA57Z60, JANSR2N7467U2

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

**Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation** <sup>⑤⑥</sup>

	Parameter	Up to 500K Rads(Si) <sup>1</sup>		1000K Rads (Si) <sup>2</sup>		Units	Test Conditions
		Min	Max	Min	Max		
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	30	—	30	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1.0mA
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	4.0	1.5	4.0		V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 1.0mA
I <sub>GSS</sub>	Gate-to-Source Leakage Forward	—	100	—	100	nA	V <sub>GS</sub> = 20V
I <sub>GSS</sub>	Gate-to-Source Leakage Reverse	—	-100	—	-100		V <sub>GS</sub> = -20 V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	—	10	—	25	μA	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V
R <sub>DS(on)</sub>	Static Drain-to-Source <sup>④</sup> On-State Resistance (TO-3)	—	0.004	—	0.0045	Ω	V <sub>GS</sub> = 12V, I <sub>D</sub> =45A
R <sub>DS(on)</sub>	Static Drain-to-Source <sup>④</sup> On-State Resistance (SMD-2)	—	0.0035	—	0.004	Ω	V <sub>GS</sub> = 12V, I <sub>D</sub> =45A
V <sub>SD</sub>	Diode Forward Voltage <sup>④</sup>	—	1.3	—	1.3	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 45A

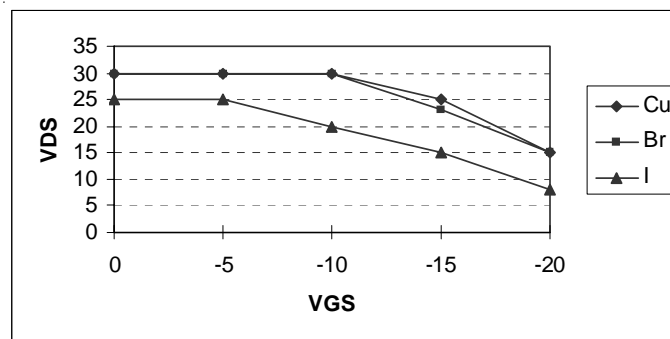
1. Part numbers IRHNA57Z60 (JANSR2N7467U2), IRHNA53Z60 (JANSF2N7467U2) and IRHNA54Z60 (JANSR2N7467U2)

2. Part number IRHNA58Z60 (JANSH2N7467U2)

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

**Table 2. Single Event Effect Safe Operating Area**

Ion	LET (MeV/(mg/cm <sup>2</sup> ))	Energy (MeV)	Range (μm)	V <sub>DS</sub> (V)				
				@V <sub>GS</sub> =0V	@V <sub>GS</sub> =-5V	@V <sub>GS</sub> =-10V	@V <sub>GS</sub> =-15V	@V <sub>GS</sub> =-20V
Cu	28	261	40	30	30	30	25	15
Br	37	285	37	30	30	30	23	15
I	60	344	33	25	25	20	15	8



**Fig a. Single Event Effect, Safe Operating Area**

For footnotes refer to the last page

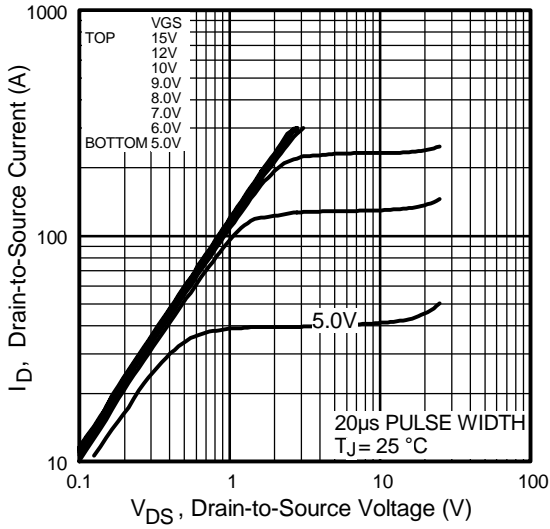


Fig 1. Typical Output Characteristics

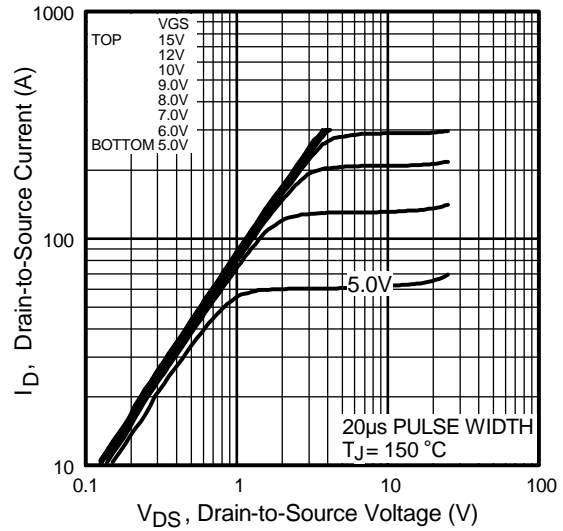


Fig 2. Typical Output Characteristics

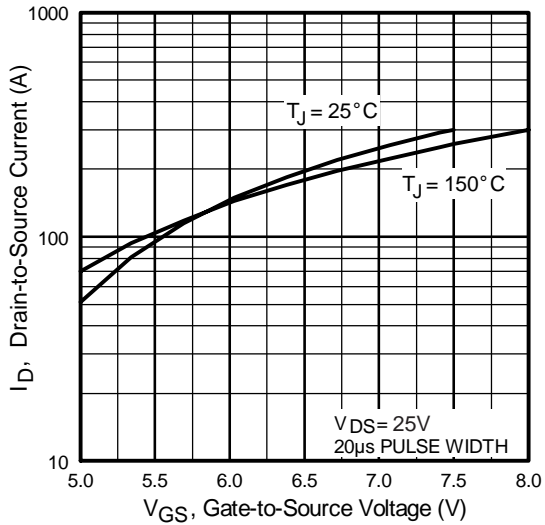


Fig 3. Typical Transfer Characteristics

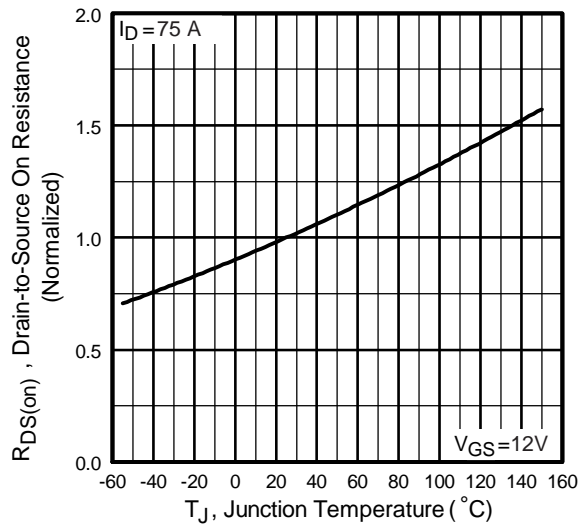


Fig 4. Normalized On-Resistance Vs. Temperature

Pre-Irradiation

IRHNA57Z60, JANSR2N7467U2

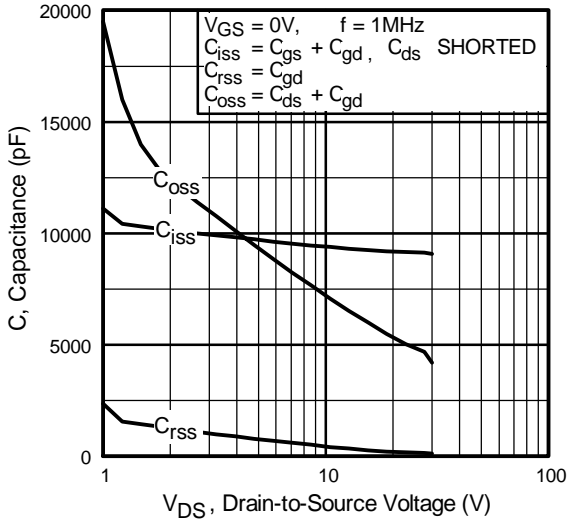


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

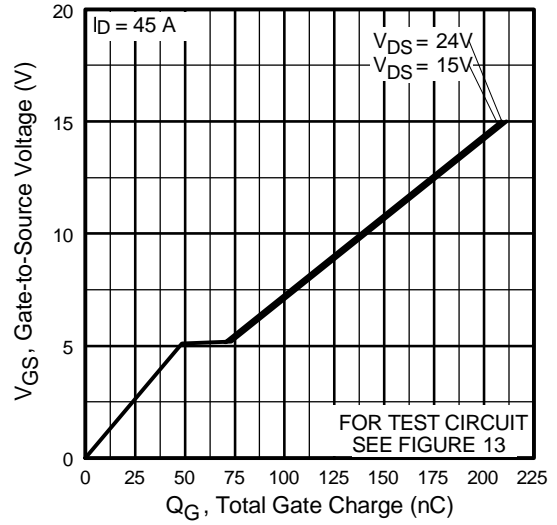


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

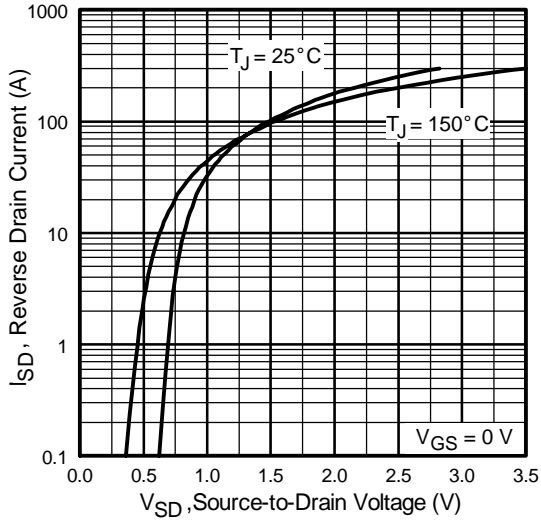


Fig 7. Typical Source-Drain Diode Forward Voltage

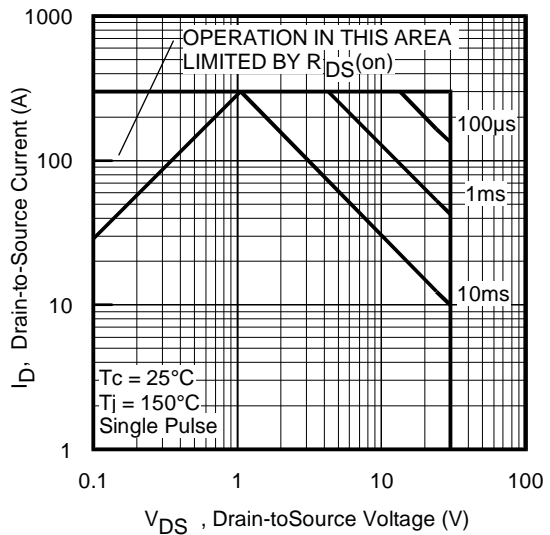


Fig 8. Maximum Safe Operating Area

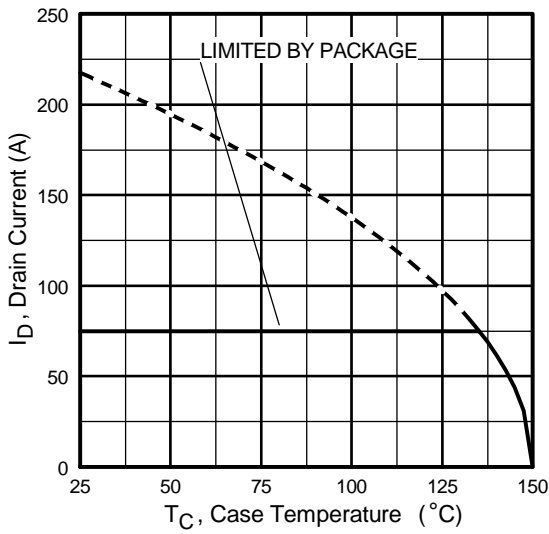


Fig 9. Maximum Drain Current Vs. Case Temperature

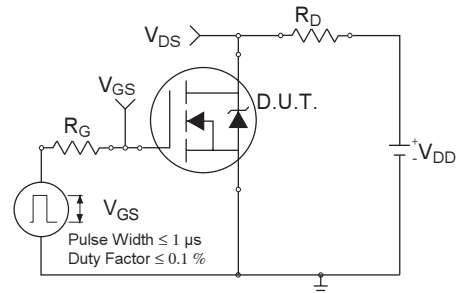


Fig 10a. Switching Time Test Circuit

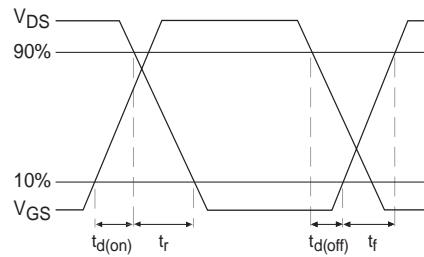


Fig 10b. Switching Time Waveforms

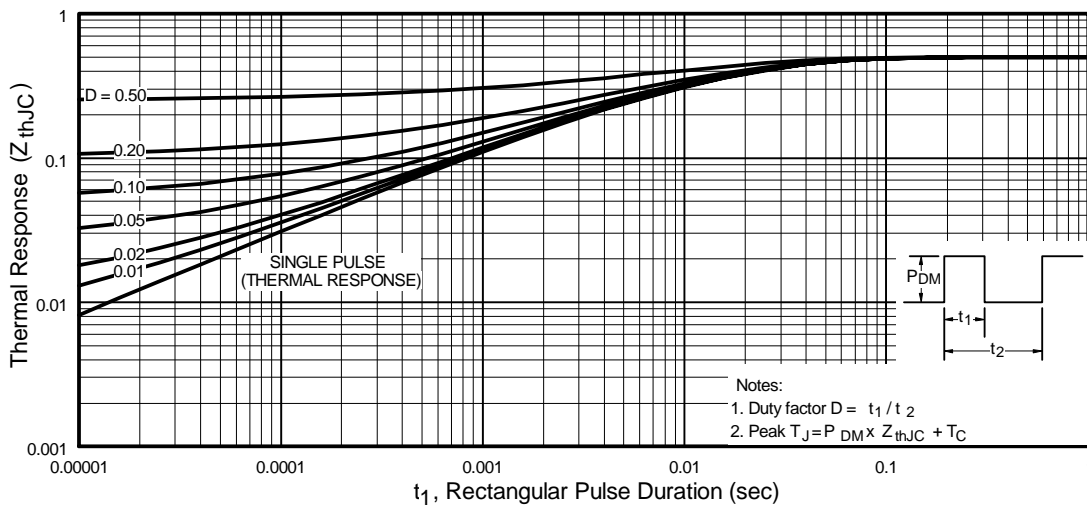


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

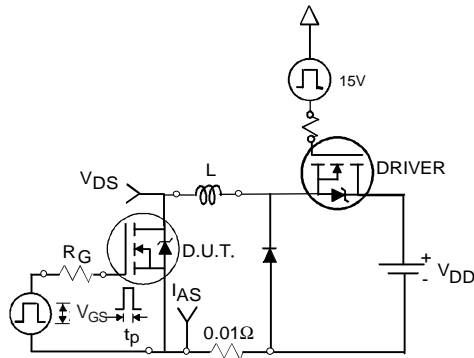


Fig 12a. Unclamped Inductive Test Circuit

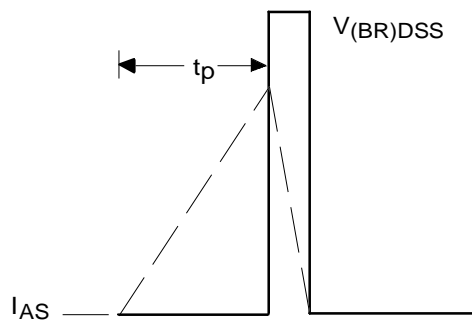


Fig 12b. Unclamped Inductive Waveforms

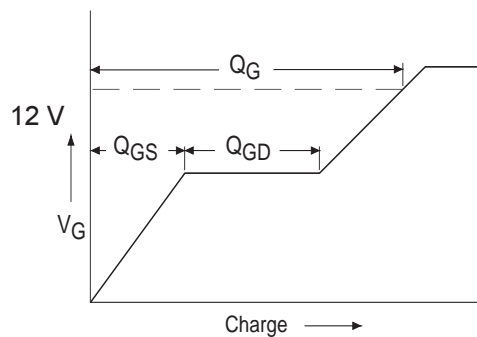


Fig 13a. Basic Gate Charge Waveform

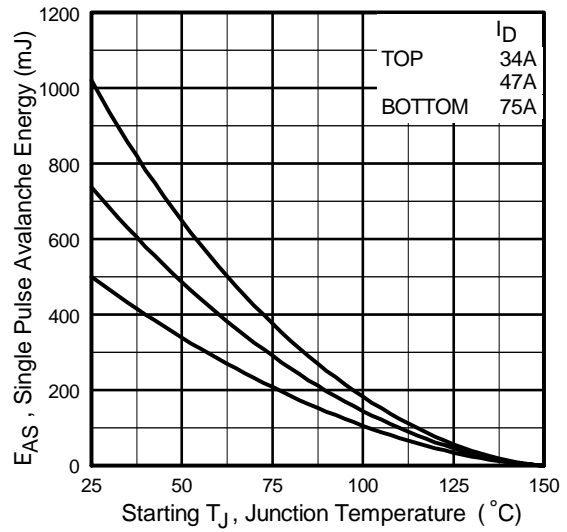


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

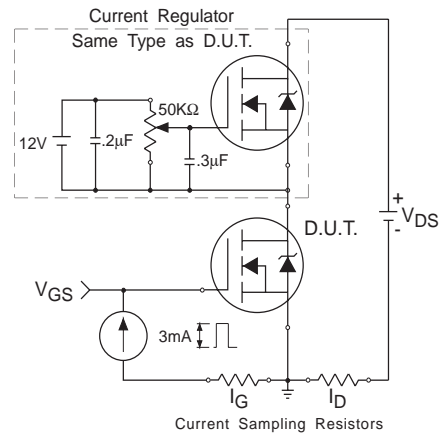
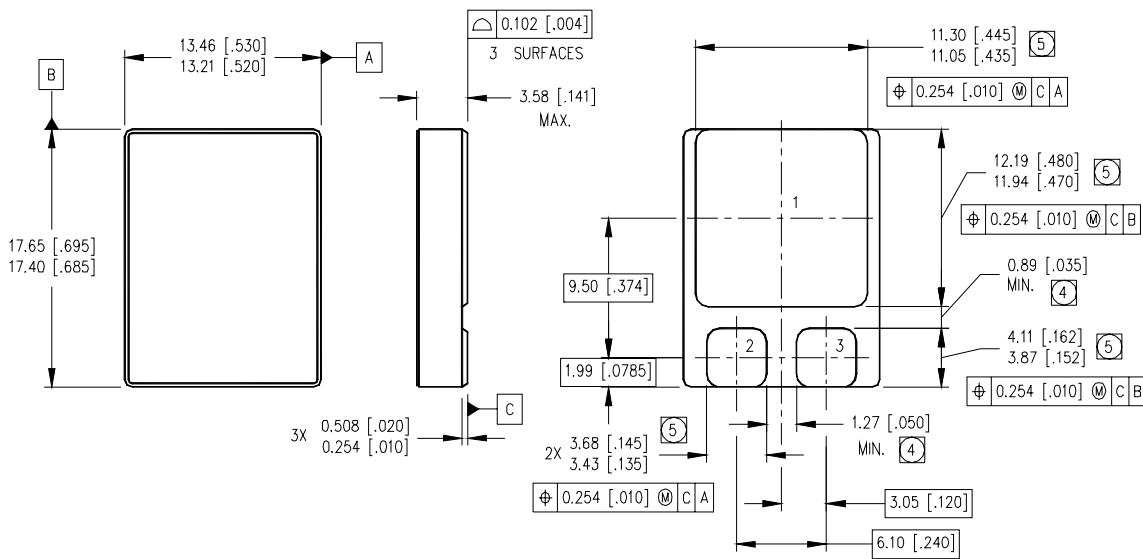


Fig 13b. Gate Charge Test Circuit

**Footnotes:**

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ②  $V_{DD} = 25V$ , starting  $T_J = 25^\circ C$ ,  $L = 0.3mH$   
Peak  $I_L = 75A$ ,  $V_{GS} = 12V$
- ③  $I_{SD} \leq 75A$ ,  $di/dt \leq 94A/\mu s$ ,  
 $V_{DD} \leq 30V$ ,  $T_J \leq 150^\circ C$
- ④ Pulse width  $\leq 300 \mu s$ ; Duty Cycle  $\leq 2\%$
- ⑤ **Total Dose Irradiation with  $V_{GS}$  Bias.**  
12 volt  $V_{GS}$  applied and  $V_{DS} = 0$  during irradiation per MIL-STD-750, method 1019, condition A.
- ⑥ **Total Dose Irradiation with  $V_{DS}$  Bias.**  
24 volt  $V_{DS}$  applied and  $V_{GS} = 0$  during irradiation per MIL-STD-750, method 1019, condition A.

**Case Outline and Dimensions — SMD-2**



NOTES:

- 1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
- 2. CONTROLLING DIMENSION: INCH.
- 3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- ④ DIMENSION INCLUDES METALLIZATION FLASH.
- ⑤ DIMENSION DOES NOT INCLUDE METALLIZATION FLASH.

PAD ASSIGNMENTS

- 1 = DRAIN
- 2 = GATE
- 3 = SOURCE

International  
**IR** Rectifier

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Data and specifications subject to change without notice. 04/2006